## MSKSEMI















**ESD** 

TVS

TSS

MOV

GDT

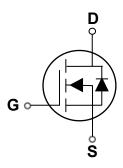
**PLED** 

# Broduct data sheet





SOT-23-3L



#### **Features**

- 100V, 1.3A , RDS(ON)=500mΩ @ VGS=10V
- Improved dv/dt capability
- Fast switching
- Green Device Available

#### **Applications**

- Networking
- Load Switch
- LED applications

BVDSS	RDSON	ID
100V	$500 \mathrm{m}\Omega$	1.3A

#### Absolute Maximum Ratings Tc=25°C unless otherwise noted

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	100	V
<b>V</b> GS	Gate-Source Voltage	±20	V
	Drain Current − Continuous (T <sub>A</sub> =25°C)	1.3	А
lo	Drain Current − Continuous (T <sub>A</sub> =70°C)	1.12	А
<b>І</b> рм	Drain Current – Pulsed¹	5.6	А
D	Power Dissipation (T <sub>A</sub> =25°C)	1.56	W
Po	Power Dissipation – Derate above 25℃	0.012	W/°C
Гѕтс	Storage Temperature Range	-50 to 150	℃
TJ	Operating Junction Temperature Range	-50 to 150	℃

#### **Thermal Characteristics**

Symbol	Parameter	Тур.	Max.	Unit
Reja	Thermal Resistance Junction to ambient		80	°C/W



#### **Off Characteristics**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BVDSS	Drain- Source Breakdown Voltage V <sub>GS</sub> =0V , I <sub>D</sub> =250uA		100			٧
△BV <sub>DSS</sub> /△T <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C , I <sub>D</sub> =1mA		0.09		V/°C
1	Drain- Source Leakage Current	V <sub>DS</sub> =100V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C			1	uĄ
loss Drain-Source Leakage Current		V <sub>DS</sub> =80V , V <sub>GS</sub> =0V , T <sub>J</sub> =125°C			10	uд
Igss	Gate- Source Leakage Current	Vgs= ±20V , Vps=0V			± 100	nĄ

#### **On Characteristics**

	RDS(ON)	Static Drain-Source On-Resistance	Vgs=10V , ID=1A		500	600	mΩ
			Vgs=4 .5V , Ip =0.5A		550	700	mΩ
	$V_{\text{GS(th)}}$	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250 uA		1.6	2.5	V
	$\triangle V_{\text{GS(th)}}$	V <sub>GS(th)</sub> Temperature Coefficient			-5		mV/°C
	gfs	Forward Transconductance	V <sub>DS</sub> =10V , I <sub>D</sub> =1A		2.3		S

#### **Dynamic and switching Characteristics**

Qg	Total Gate Charge <sup>2</sup> · <sup>3</sup>		 9	
Qgs	Gate-Source Charge <sup>2</sup> , <sup>3</sup>	VDS=50V , VGS=10V , ID=1A	 2.3	 nC
Qgd	Gate-Drain Charge <sup>2, 3</sup>		 1.1	
T <sub>d(on)</sub>	Turn-On Delay Time <sup>2</sup> · <sup>3</sup>		 5.2	
Tr	Rise Time <sup>2 · 3</sup>	$V_{DD}$ =50 $V$ , $V_{GS}$ =10 $V$ , $R_{G}$ =3.3 $\Omega$	 6.8	 
T <sub>d(off)</sub>	Turn-Off Delay Time <sup>2</sup> · <sup>3</sup>	I <sub>D</sub> =1A	 14.5	 ns
Tf	Fall Time <sup>2</sup> , <sup>3</sup>		 2.1	
Ciss	Input Capacitance		 492	
Coss	Output Capacitance	V <sub>DS</sub> =25V , V <sub>GS</sub> =0V , F=1MHz	 27	 PF
Crss	Reverse Transfer Capacitance		 15	

#### **Drain-Source Diode Characteristics and Maximum Ratings**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
ls	Continuous Source Current	V = V = 0.V			13	Α
lsм	Pulsed Source Current	V <sub>G</sub> =V <sub>D</sub> =0 V , Force Current			2.6	Α
Vsp	Diode Forward Voltage	V <sub>G</sub> s=0V , I <sub>S</sub> =1A , T <sub>J</sub> =25°C			1.2	V

#### Note :

- 1. Repetitive Rating: Pulsed width limited by maximum junction temperature.
- 2 . The data tested by pulsed , pulse width  $\leq 300\,\mathrm{us}$  , duty cycle  $\leq 2\%$  .
- 3. Essentially independent of operating temperature.



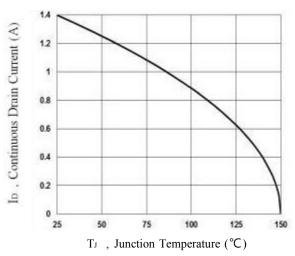


Fig. 1 Continuous Drain Current vs. T<sub>J</sub>

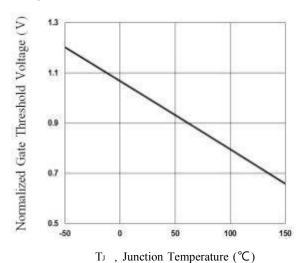


Fig. 3 Normalized V<sub>th</sub> vs. T<sub>J</sub>

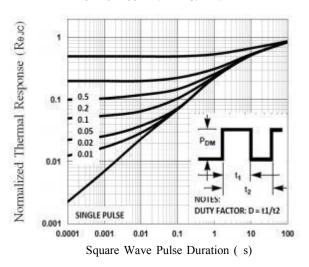


Fig. 5 Normalized Transient Impedance

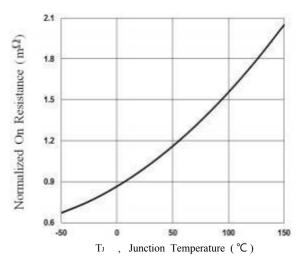


Fig. 2 Normalized RDSON vs. T<sub>J</sub>

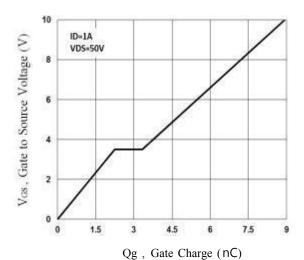


Fig. 4 Gate Charge Waveform

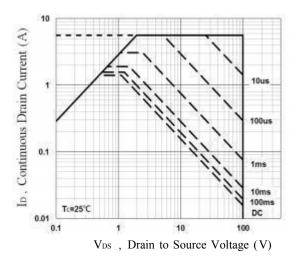
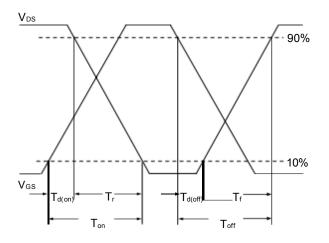


Fig. 6 Maximum Safe Operation Area





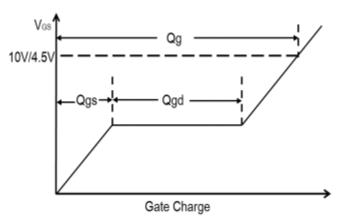


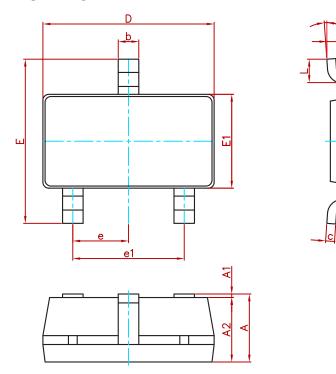
Fig. 7 Switching Time Waveform

Fig. 8 Gate Charge Waveform



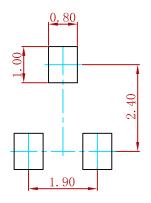
0.200

#### **PACKAGE MECHANICAL DATA**



Symbol	Dimensions In Millimeters		Dimension	s In Inches
Symbol	Min.	Max.	Min.	Max.
Α	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
С	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
е	0.950(BSC)		0.037(	(BSC)
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

### **Suggested Pad Layout**



- 1.Controlling dimension:in millimeters.
  2.General tolerance:± 0.05mm.
  3.The pad layout is for reference purposes only.

#### **REEL SPECIFICATION**

P/N	PKG	QTY
AO3442	SOT-23-3L	3000



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